

Declaration of Compliance

Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 and Delegated Directive (EU) 2015/863 of the European Parliament and Council of March 31, 2015, on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Regulatory Model	Product Name
NXS1U1NS12G800 *	Converged Server/Storage System

^{*} NXS1U1NS12G800 will cover NX-3170-G8 models and its Options (Part numbers starting with C-), Upgrades (Part numbers starting with U-) and Spares/FRU (Part numbers starting with X-).

The above listed product or product family has been verified to be **in compliance** with the European Union Restriction of Hazardous Substances, Directive 2011/65/EU and Delegated Directive (EU) 2015/863.

This declaration is based in part on information provided to Nutanix by its suppliers. To the best of our knowledge, the above listed product does not contain Lead (0.1 % w/w), Mercury (0.1 % w/w), Cadmium (0.01 % w/w), Hexavalent chromium (0.1 % w/w), Polybrominated biphenyls (PBB) (0.1 % w/w), Polybrominated diphenyl ethers (PBDE) (0.1 % w/w), Bis(2-Ethylhexyl) phthalate (DEHP) (0.1 % w/w), Benzyl butyl phthalate (BBP) (0.1 % w/w), Dibutyl phthalate (DBP) (0.1 % w/w), or Diisobutyl phthalate (DIBP) (0.1 % w/w) except where valid exemptions have been granted by the European Union.

The following exemptions were used to achieve compliance:

6a(i). Lead as an alloying element in steel for machining purposes containing up to 0.35% lead by weight and in batch hot dip galvanised steel components containing up to 0.2% lead by weight 6b(ii). Lead as an alloying element in aluminium for machining purposes with a lead content up to 0.4% by weight \boxtimes 6c. Copper alloy containing up to 4 % lead by weight \boxtimes 7a. Lead in high melting temperature type solders (i.e. lead-based alloys containing 85% by weight or more lead) \boxtimes 7c(i). Electrical and electronic components containing lead in a glass or ceramic other than dielectric ceramic in capacitors, e.g. piezoelectronic devices, or in a glass or ceramic matrix compound 13(a). Lead in white glasses used for optical applications П 15(a). Lead in solders to complete a viable electrical connection between the semiconductor die and carrier within integrated circuit flip chip packages where at least one of the following criteria applies: A semiconductor technology node of 90 nm or larger.

Stacked die packages with die of 300 mm² or larger, or silicon interposers of 300 mm² or larger.

A single die of 300 mm² or larger in any semiconductor technology node.

Ashok Sarathy

Sr. Director, Quality Engineering September 17, 2021